

Preliminary Amendment

In Specification

Please amend the Specification as follows:

- 1) p.3, line 19-20, delete "...increasing temperature of the aqueous solution" and add "conducting a first step of maintaining the solution at a first temperature for a first preset time, a second step of increasing the temperature of the solution from the first temperature to a second higher temperature for a second preset time and a third step of maintaining the solution at the second temperature for a third preset time."
- 2) P.4, between line 5 and line 6 insert a sentence "In this case, according to the present invention, a buffer layer is formed of stepwise deposits particles of n-type semiconductor material in such manner as the layer has a profile which represents deposits having different pH-values: upper deposits have larger pH value."
- 3) P.13, line 6, after "...layer" insert "or featured by a structure having upper side deposits of larger pH-values and lower side deposits of smaller pH values".

In Claims:

- 4) Please cancel claims 1, 5, 7 and 9.
- 5) Please rewrite claim 2 as follows:

(Amended) A method of fabricating a thin-film compound solar cell having an n-type buffer layer formed therein for providing a heterojunction with a p-type semiconductor light absorbing layer formed on a back electrode, wherein the buffer layer is formed on the light absorbing layer by chemical bath deposition (CBD) process using an aqueous solution for dipping therein a surface of the light absorbing layer, wherein the CBD process comprises a first step of holding the solution with the light absorbing layer surface dipped therein at a first preset temperature for a first preset time, a second step of heating the solution for a second preset time to a second temperature higher than the first temperature and a third step of holding the solution at the second temperature for a third preset time.

6) Please rewrite claim 3 as follows:

(Amended) A method of fabricating a thin-film compound solar cell as defined in claim 2, wherein the aqueous solution is stirred all for the first, second and third steps.

7) Please rewrite Claim 4 as follows:

(Amended) A method of fabricating a thin-film compound solar cell having an n-type buffer layer formed therein for providing a heterojunction with a p-type semiconductor light absorbing layer formed on a back electrode, wherein the buffer layer is formed on the

light absorbing layer by chemical bath deposition (CBD) process using an aqueous solution for dipping therein a surface of the light absorbing layer, wherein, in the CBD process of forming the buffer layer on the light absorbing layer whose surface is dipped in an aqueous solution for depositing particles thereon, pH of the solution is changed from a low level to a high level to cause the buffer layer to have different quality of deposit layers therein.

8) Please rewrite claim 6 as follows:

(Amended) A method of fabricating a thin-film compound solar cell as defined in claim 2, wherein pH of the aqueous solution is regulated to a higher value in the third step.

9) Please rewrite claim 8 as follows:

(Amended) A method of fabricating a thin-film compound solar cell having an n-type buffer layer formed therein for providing a heterojunction with a p-type semiconductor light absorbing layer formed on a back electrode, wherein the buffer layer is formed of layered deposits of particles of n-type semiconductor material and the layered deposits are different from each other by grain sizes gradually or stepwise increasing in the deposits in a direction outward from the light absorbing layer.

10) Please amend claim 10 as follows:

3. A method of fabricating a thin-film compound solar cell having an n-type buffer layer formed therein for providing heterojunction with a p-type semiconductor light absorbing layer formed on a back electrode, wherein the buffer layer is formed of layered deposits of particles of n-type semiconductor material and the layered deposits are different from each other by pH-values being smaller in lower side deposit and larger in upper side deposit in a profile of the buffer layer.